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FAIRCHILD SEMICONDUCTOR®

July 2010

FDME1024NZT

Dual N-Channel PowerTrench® MOSFET

20 V, 3.8 A, 66 mΩ

Features

- Max $r_{DS(on)}$ = 66 mΩ at V_{GS} = 4.5 V, I_D = 3.4 A
- Max $r_{DS(on)}$ = 86 mΩ at V_{GS} = 2.5 V, I_D = 2.9 A
- Max $r_{DS(on)}$ = 113 mΩ at V_{GS} = 1.8 V, I_D = 2.5 A
- Max $r_{DS(on)}$ = 160 mΩ at V_{GS} = 1.5 V, I_D = 2.1 A
- Low profile: 0.55 mm maximum in the new package MicroFET 1.6x1.6 **Thin**
- Free from halogenated compounds and antimony oxides
- HBM ESD protection level > 1600 V (Note 3)
- RoHS Compliant

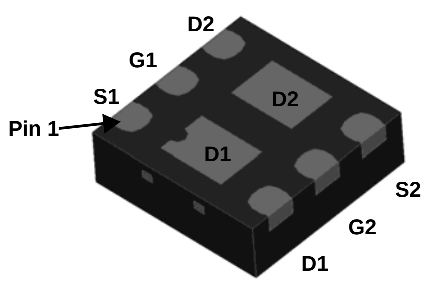
General Description

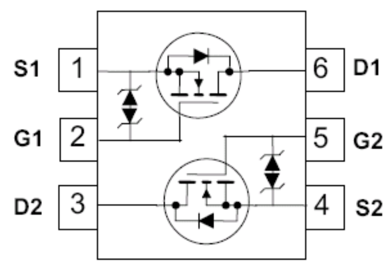
This device is designed specifically as a single package solution for dual switching requirement in cellular handset and other ultra-portable applications. It features two independent N-Channel MOSFETs with low on-state resistance for minimum conduction losses.

The MicroFET 1.6x1.6 **Thin** package offers exceptional thermal performance for it's physical size and is well suited to switching and linear mode applications.

Applications

- Baseband Switch
- Load Switch





BOTTOM **TOP**

MicroFET 1.6x1.6 Thin

MOSFET Maximum Ratings T_A = 25 °C unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DS}	Drain to Source Voltage	20	V
V_{GS}	Gate to Source Voltage	±8	V
I_D	Drain Current -Continuous T_A = 25 °C (Note 1a)	3.8	A
	-Pulsed	6	
P_D	Power Dissipation for Single Operation T_A = 25 °C (Note 1a)	1.4	W
	Power Dissipation for Single Operation T_A = 25 °C (Note 1b)	0.6	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Single Operation) (Note 1a)	90	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Single Operation) (Note 1b)	195	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
4T	FDME1024NZT	MicroFET 1.6x1.6 **Thin**	7 ”	8 mm	5000 units

Electrical Characteristics T_J = 25 °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units

Off Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250 μA, V_{GS} = 0 V	20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25 °C		16		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 16 V, V_{GS} = 0 V			1	μA
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±8 V, V_{DS} = 0 V			±10	μA

On Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, I_D = 250 μA	0.4	0.7	1.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25 °C		-3		mV/°C
$r_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 4.5 V, I_D = 3.4 A		55	66	mΩ
		V_{GS} = 2.5 V, I_D = 2.9 A		68	86	
		V_{GS} = 1.8 V, I_D = 2.5 A		85	113	
		V_{GS} = 1.5 V, I_D = 2.1 A		106	160	
		V_{GS} = 4.5 V, I_D = 3.4 A, T_J = 125 °C		76	112	
g_{FS}	Forward Transconductance	V_{DD} = 4.5 V, I_D = 3.4 A		9		S

Dynamic Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
C_{iss}	Input Capacitance	V_{DS} = 10 V, V_{GS} = 0 V, f = 1 MHz		225	300	pF
C_{oss}	Output Capacitance			40	55	pF
C_{rss}	Reverse Transfer Capacitance			25	40	pF

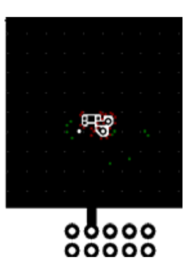
Switching Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 10 V, I_D = 1 A, V_{GS} = 4.5 V, R_{GEN} = 6 Ω		4.5	10	ns
t_r	Rise Time			2	10	ns
$t_{d(off)}$	Turn-Off Delay Time			15	27	ns
t_f	Fall Time			1.7	10	ns
Q_g	Total Gate Charge	V_{DD} = 10 V, I_D = 3.4 A, V_{GS} = 4.5 V		3	4.2	nC
Q_{gs}	Gate to Source Gate Charge			0.4		nC
Q_{gd}	Gate to Drain “Miller” Charge			0.6		nC

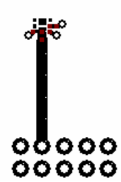
Drain-Source Diode Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0 V, I_S = 0.9 A (Note 2)		0.7	1.2	V
t_{rr}	Reverse Recovery Time	I_F = 3.4 A, di/dt = 100 A/μs		8.5	17	ns
Q_{rr}	Reverse Recovery Charge			1.4	10	nC

NOTES:
1. $R_{\theta JA}$ is determined with the device mounted on a 1 in^2 pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a. 90 °C/W when mounted on a 1 in^2 pad of 2 oz copper.



b. 195 °C/W when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0%.
3. The diode connected between the gate and source serves only as protection ESD. No gate overvoltage rating is implied.

Typical Characteristics T_J = 25 °C unless otherwise noted

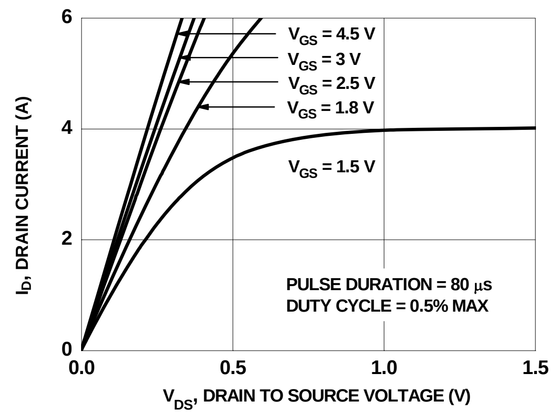


Figure 1. On-Region Characteristics

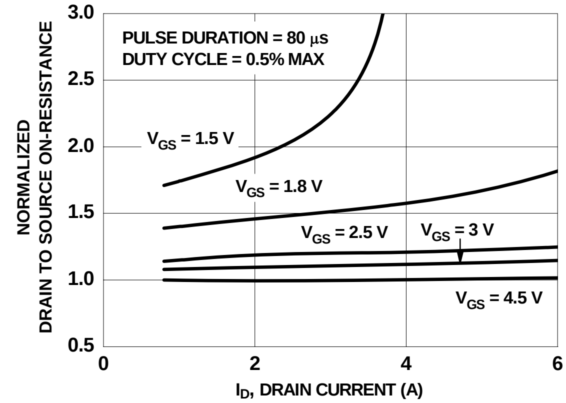


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

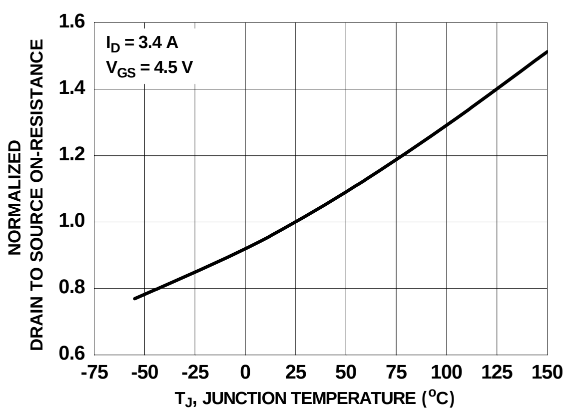


Figure 3. Normalized On-Resistance vs Junction Temperature

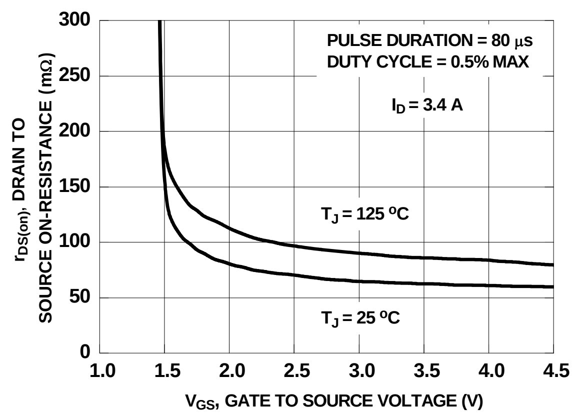


Figure 4. On-Resistance vs Gate to Source Voltage

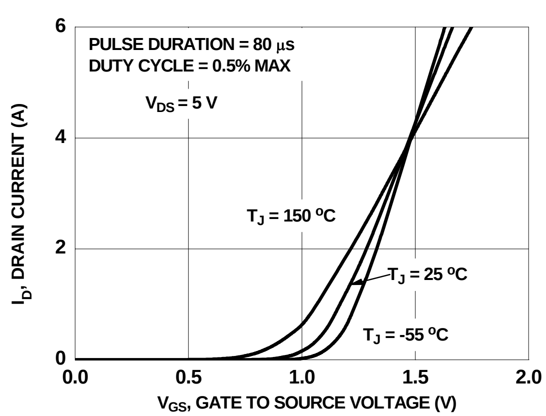


Figure 5. Transfer Characteristics

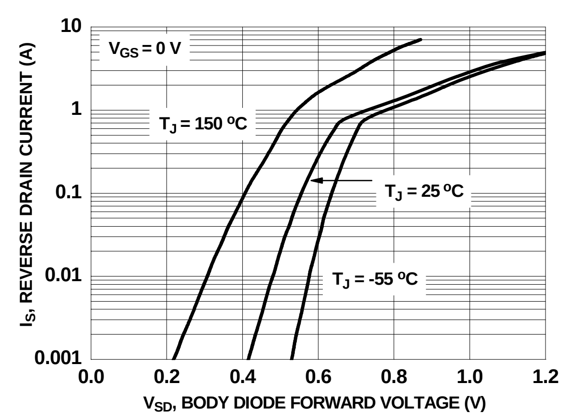


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics T_J = 25 °C unless otherwise noted

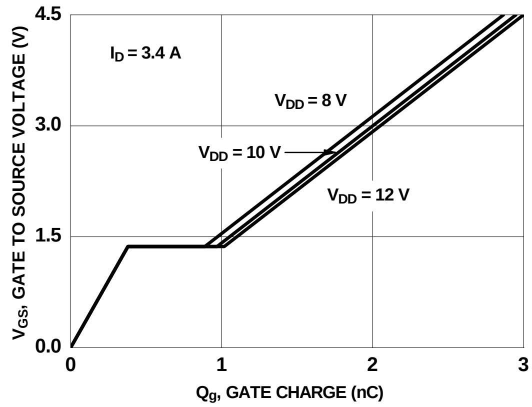


Figure 7. Gate Charge Characteristics

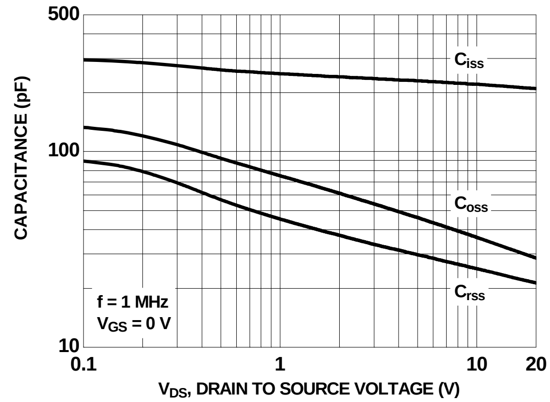


Figure 8. Capacitance vs Drain to Source Voltage

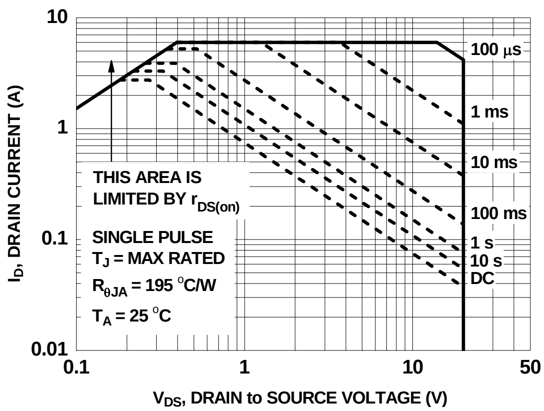


Figure 9. Forward Bias Safe Operating Area

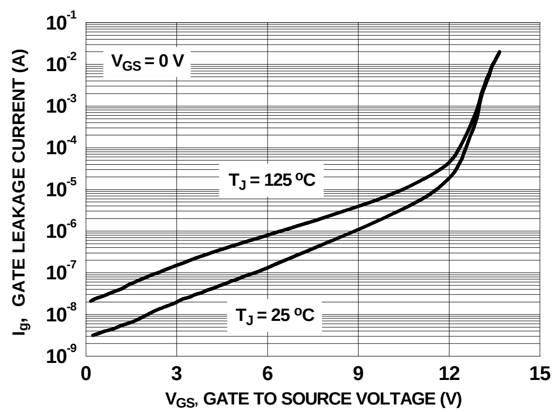


Figure 10. Gate Leakage Current vs Gate to Source Voltage

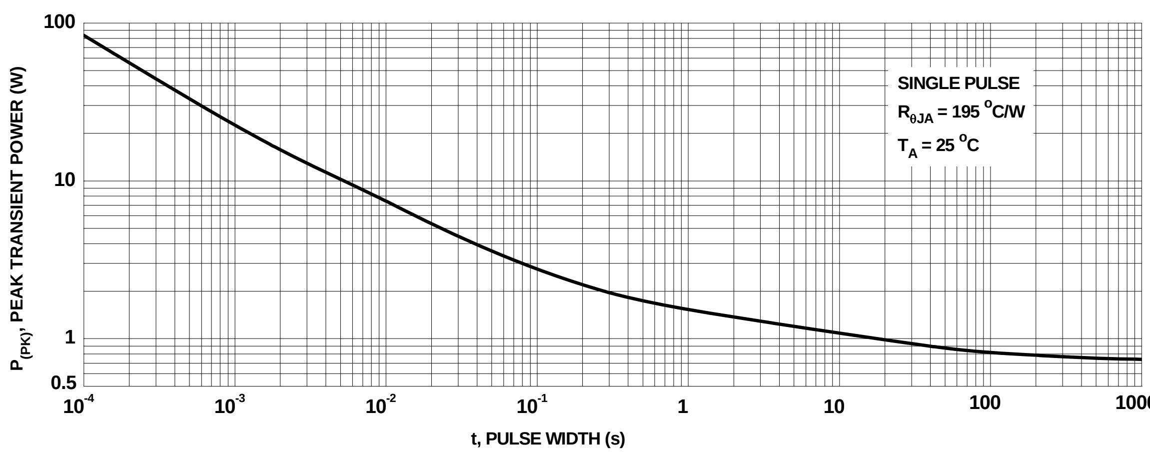


Figure 11. Single Pulse Maximum Power Dissipation

Typical Characteristics T_J = 25 °C unless otherwise noted

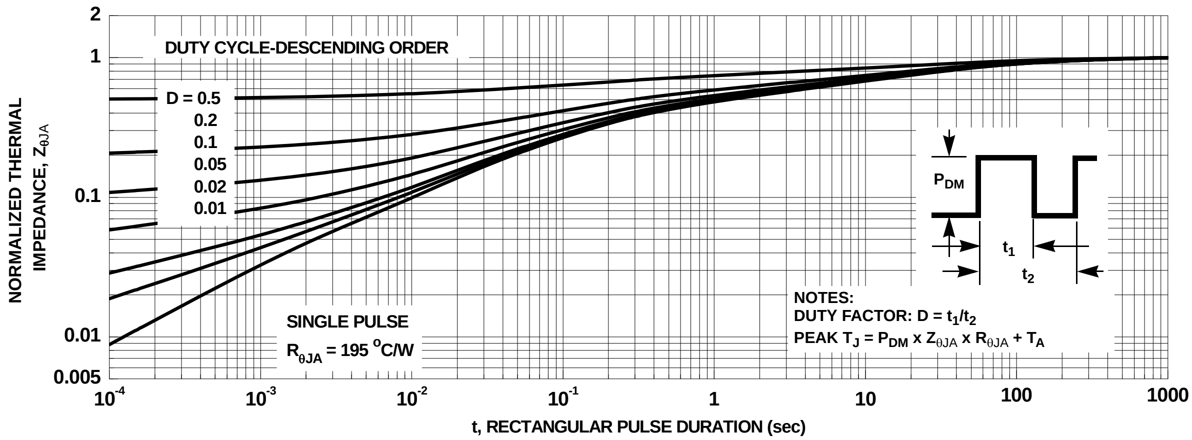
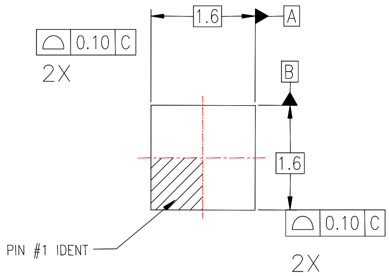
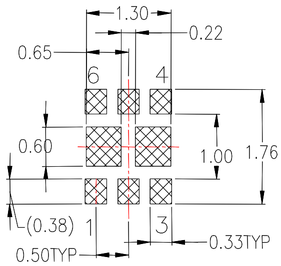


Figure 12. Junction-to-Ambient Transient Thermal Response Curve

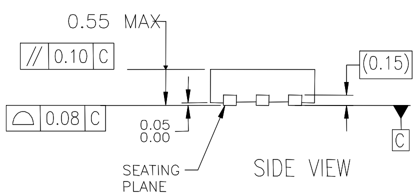
Dimensional Outline and Pad Layout



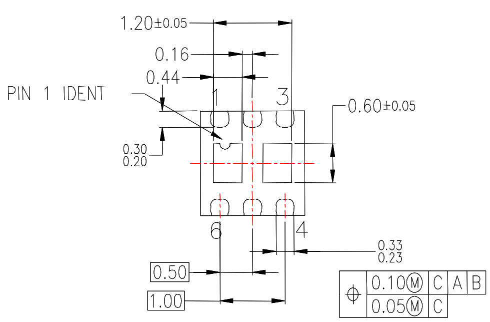
TOP VIEW



RECOMMENDED LAND PATTERN



SIDE VIEW



BOTTOM VIEW

FDME1024NZT Dual N-Channel PowerTrench® MOSFET

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